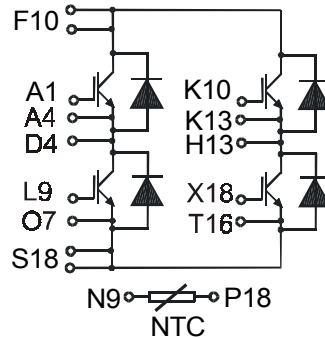


IGBT Module PSHI 100/06* H-Bridge Configuration

Preliminary Data Sheet

Short Circuit SOA Capability
Square RBSOA



$I_{C25} = 69 \text{ A}$
 $V_{CES} = 600 \text{ V}$
 $V_{CE(sat)typ.} = 2.3 \text{ V}$



PSHI 100/06*

*NTC optional

IGBTs

| Symbol | Conditions | Maximum Ratings | |
|-----------------------|--|-----------------|---------------|
| V_{CES} | $T_{VJ} = 25^\circ\text{C to } 150^\circ\text{C}$ | 600 | V |
| V_{GES} | | ± 20 | V |
| I_{C25} | $T_C = 25^\circ\text{C}$ | 69 | A |
| I_{C80} | $T_C = 80^\circ\text{C}$ | 48 | A |
| I_{CM} V_{CEK} | $V_{GE} = \pm 15 \text{ V}; R_G = 22 \Omega; T_{VJ} = 125^\circ\text{C}$ RBSOA, Clamped inductive load; $L = 100 \mu\text{H}$ | 100 | A |
| | | V_{CES} | |
| t_{SC} (SCSOA) | $V_{CE} = V_{CES}; V_{GE} = \pm 15 \text{ V}; R_G = 22 \Omega; T_{VJ} = 125^\circ\text{C}$ non-repetitive | 10 | μs |
| P_{tot} | $T_C = 25^\circ\text{C}$ | 208 | W |

Features

- NPT IGBT technology
- low saturation voltage
- low switching losses
- square RBSOA, no latch up
- high short circuit capability
- positive temperature coefficient for easy paralleling
- MOS input, voltage controlled
- ultra fast free wheeling diodes
- solderable pins for PCB mounting
- package with copper base plate
- Isolation voltage 3000 V~
- UL registered, E 148688

| Symbol | Conditions | Characteristic Values ($T_{VJ} = 25^\circ\text{C}$, unless otherwise specified) | | | |
|--|--|--|-----------------------|----------------------|-----|
| | | min. | typ. | max. | |
| $V_{CE(sat)}$ | $I_C = 75 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$ | | 2.3 2.8 | V V | |
| $V_{GE(th)}$ | $I_C = 1 \text{ mA}; V_{GE} = V_{CE}$ | 4.5 | | 6.5 V | |
| I_{CES} | $V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$ | | | 0.8 mA 4.4 mA | |
| I_{GES} | $V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$ | | | 100 nA | |
| $t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off} | Inductive load, $T_{VJ} = 125^\circ\text{C}$ $V_{CE} = 300 \text{ V}; I_C = 40 \text{ A}$ $V_{GE} = 15/0 \text{ V}; R_G = 22 \Omega$ | | 50 55 300 30 | ns ns ns ns | |
| | | | 1.8 | mJ | |
| | | | 1.4 | mJ | |
| C_{ies} | | $V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$ | | 2.8 | nF |
| R_{thJC} | | (per IGBT) | | 0.6 | K/W |
| R_{thJH} | | with heatsink compound (0.42 K/m.K; 50 μm) | 1.2 | | K/W |

Advantages

- space and weight savings
- reduced protection circuits
- package designed for wave soldering
- High power density
- Easy to mount with two screws

Typical Applications

- motor control
 - DC motor armature winding
 - DC motor excitation winding
 - synchronous motor excitation winding
- supply of transformer primary winding
 - power supplies
 - welding
 - X-ray
 - UPS
 - battery charger

Caution: These Devices are sensitive to electrostatic discharge. Users should observe proper ESD handling precautions.

Reverse diodes (FRED)

| Symbol | Conditions | Maximum Ratings | |
|-----------|--------------------------|-----------------|---|
| I_{F25} | $T_C = 25^\circ\text{C}$ | 56 | A |
| I_{F80} | $T_C = 80^\circ\text{C}$ | 35 | A |

| Symbol | Conditions | Characteristic Values | | |
|--------------------------|--|-----------------------|------|------|
| | | min. | typ. | max. |
| V_F | $I_F = 40\text{ A}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$ | 2.32 | 2.59 | V |
| | | 1.58 | | V |
| I_{RM} t_{rr} | $I_F = 30\text{ A}; di_F/dt = 500\text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C}$ $V_R = 300\text{ V}; V_{GE} = 0\text{ V}$ | 15 | | A |
| | | 70 | | ns |
| R_{thJC} R_{thJH} | with heatsink compound (0.42 K/m.K; 50 μm) | | 1.3 | K/W |
| | | 2.6 | | K/W |

Temperature Sensor NTC

| Symbol | Conditions | Characteristic Values | | |
|-------------|------------------------|-----------------------|------|------------|
| | | min. | typ. | max. |
| R_{25} | $T = 25^\circ\text{C}$ | 455 | 470 | k Ω |
| $B_{25/50}$ | | | 3474 | K |

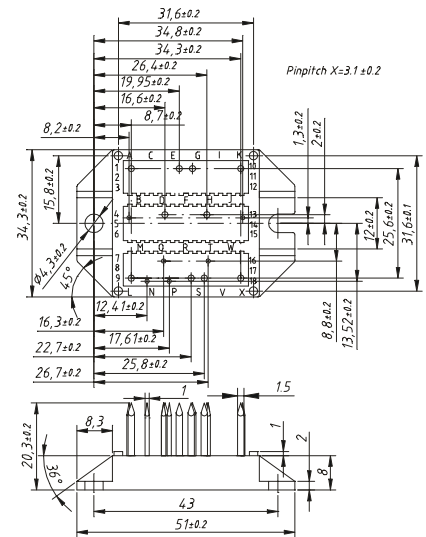
Module

| Symbol | Conditions | Maximum Ratings | |
|------------|--|-----------------|------------------|
| T_{VJ} | | -40...+150 | $^\circ\text{C}$ |
| T_{stg} | | -40...+150 | $^\circ\text{C}$ |
| V_{ISOL} | $I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}$ | 3000 | V~ |
| M_d | Mounting torque (M4) | 1.5 - 2.0 | Nm |
| | | 14 - 18 | lb.in. |
| a | Max. allowable acceleration | 50 | m/s ² |

| Symbol | Conditions | Characteristic Values | | |
|---------------|--|-----------------------|------|------|
| | | min. | typ. | max. |
| d_s | Creepage distance on surface (Pin to heatsink) | 11.2 | | mm |
| d_A | Strike distance in air (Pin to heatsink) | 11.2 | | mm |
| Weight | | 24 | | g |

Package style and outline

Dimensions in mm (1mm = 0.0394")



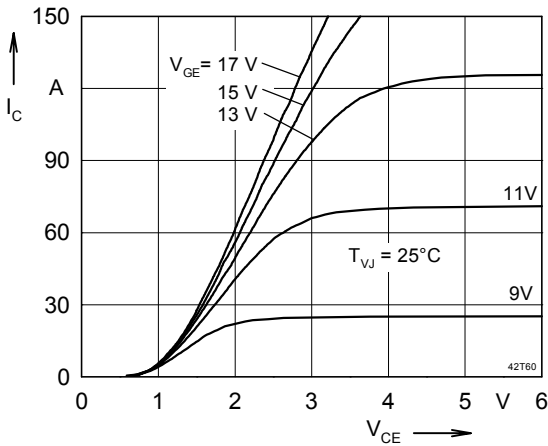


Fig. 1 Typ. output characteristics

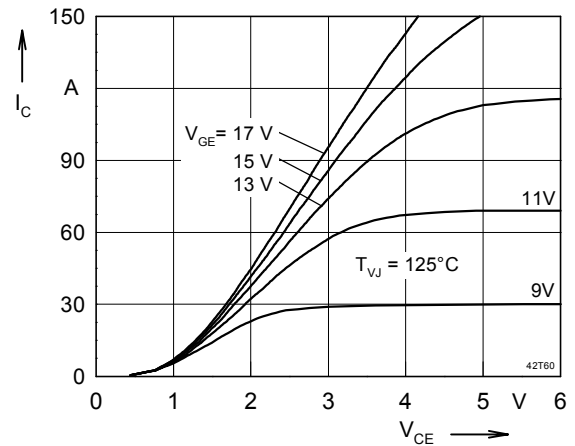


Fig. 2 Typ. output characteristics

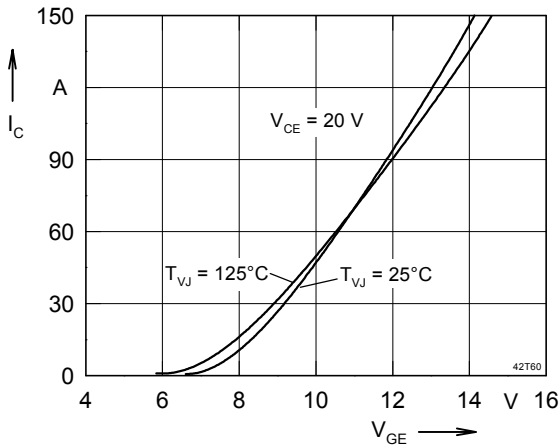


Fig. 3 Typ. transfer characteristics

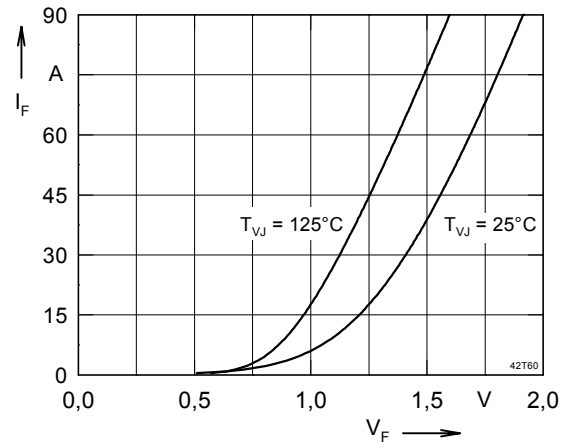


Fig. 4 Typ. forward characteristics of free wheeling diode

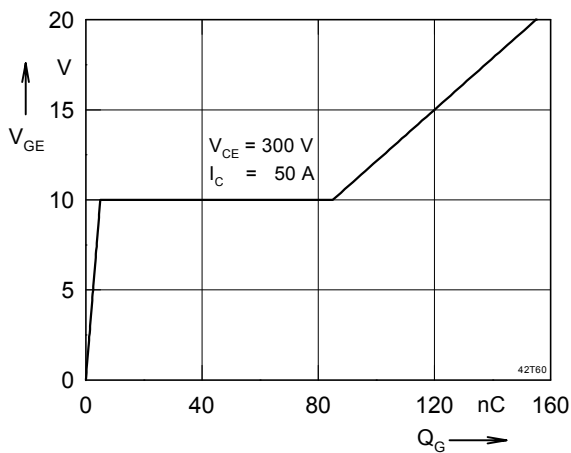


Fig. 5 Typ. turn on gate charge

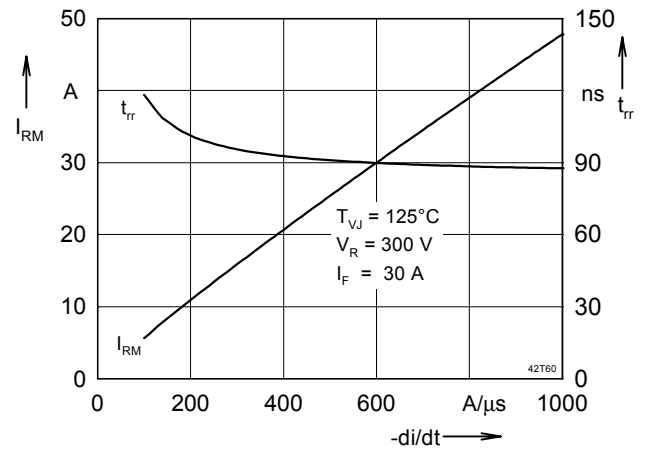


Fig. 6 Typ. turn off characteristics of free wheeling diode

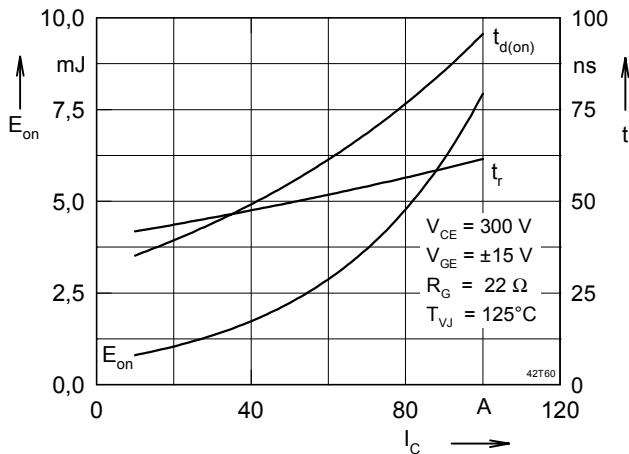


Fig. 7 Typ. turn on energy and switching

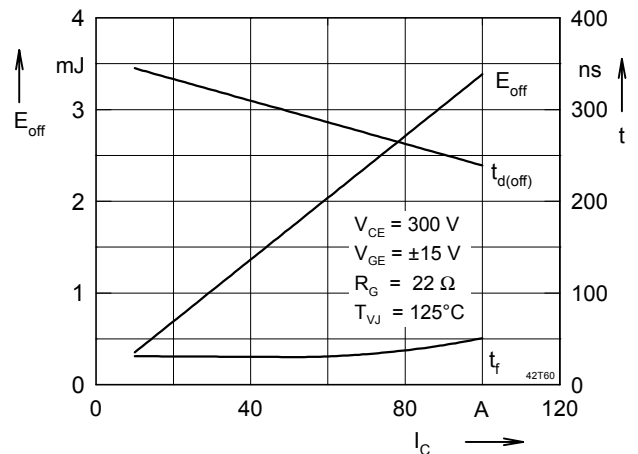


Fig. 8 Typ. turn off energy and switching times versus collector current times versus collector current

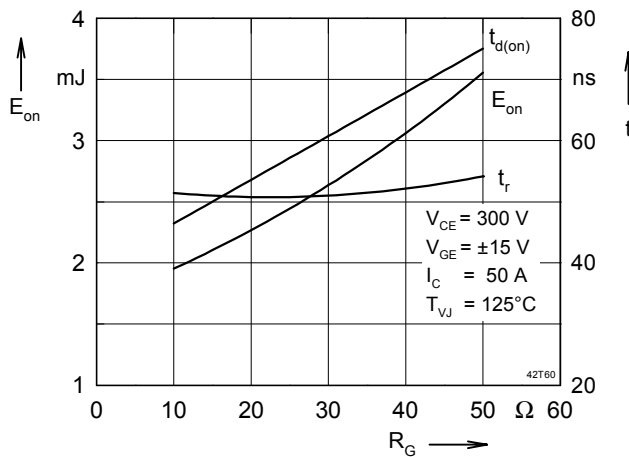


Fig. 9 Typ. turn on energy and switching

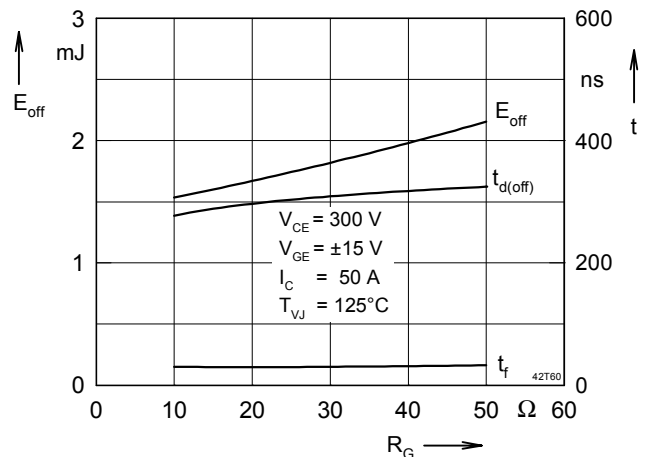


Fig. 10 Typ. turn off energy and switching times versus gate resistor times versus gate resistor

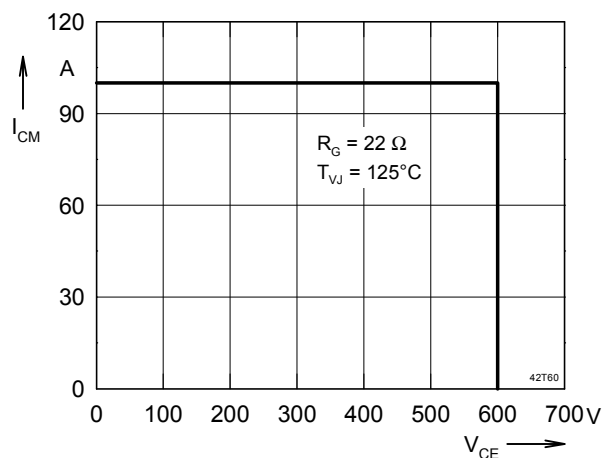


Fig. 11 Reverse biased safe operating area

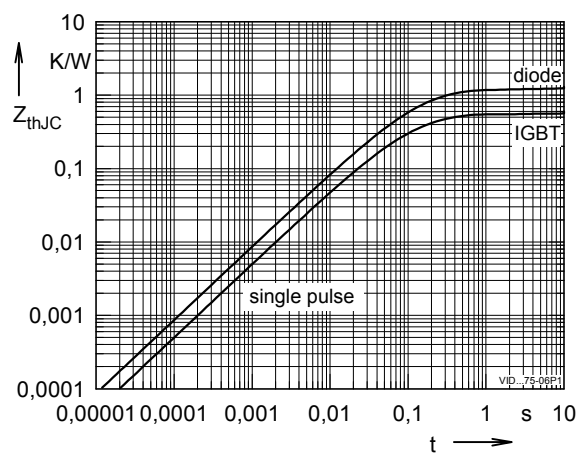


Fig. 12 Typ. transient thermal impedance RBSOA